TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC74HC132AP,TC74HC132AF,TC74HC132AFN

Quad 2-Input Schmitt NAND Gate

The TC74HC132A is a high speed CMOS 2-INPUT NAND SCHMITT TRIGGER GATE fabricated with silicon gate $\rm C^2MOS$ technology.

It achieves the high speed operation similar to equivalent LSTTL while maintaining the CMOS low power dissipation.

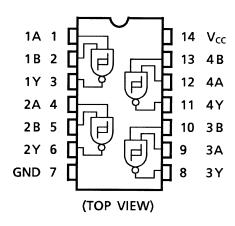
Pin configuration and function are the same as the TC74HC00A but the inputs have 25% $V_{\rm CC}$ hysteresis and with its schmitt trigger inputs, the TC74HC132A can be used as a line receiver for slow input signals.

All inputs are equipped with protection circuits against static discharge or transient excess voltage.

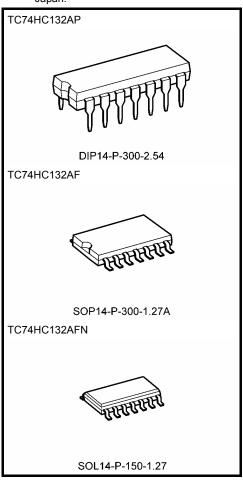
Features

- High speed: $t_{pd} = 11 \text{ ns (typ.)}$ at $V_{CC} = 5 \text{ V}$
- Low power dissipation: $I_{CC} = 1 \mu A \text{ (max)}$ at $T_{a} = 25 \text{°C}$
- High noise immunity: $V_H = 1.1 \text{ V}$ at $V_{CC} = 5 \text{ V}$
- Output drive capability: 10 LSTTL loads
- Symmetrical output impedance: $|I_{OH}| = I_{OL} = 4 \text{ mA (min)}$
- Balanced propagation delays: $t_{pLH} \approx t_{pHL}$
- Wide operating voltage range: V_{CC} (opr) = 2 to 6 V
- Pin and function compatible with 74LS132

Pin Assignment



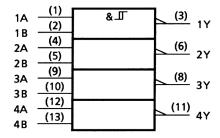
Note: xxxFN (JEDEC SOP) is not available in Japan.



Weight

DIP14-P-300-2.54 : 0.96 g (typ.) SOP14-P-300-1.27A : 0.18 g (typ.) SOL14-P-150-1.27 : 0.12 g (typ.)

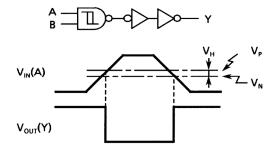
IEC Logic Symbol



Truth Table

| Α | В | Υ |
|---|---|---|
| L | L | Н |
| L | Н | Н |
| Н | L | Н |
| Н | Н | L |

System Diagram, Waveform



Absolute Maximum Ratings (Note 1)

| Characteristics | Symbol | Rating | Unit |
|------------------------------------|------------------|-------------------------------|------|
| Supply voltage range | V _{CC} | –0.5 to 7 | ٧ |
| DC input voltage | V _{IN} | −0.5 to V _{CC} + 0.5 | V |
| DC output voltage | V _{OUT} | −0.5 to V _{CC} + 0.5 | V |
| Input diode current | lık | ±20 | mA |
| Output diode current | lok | ±20 | mA |
| DC output current | lout | ±25 | mA |
| DC V _{CC} /ground current | Icc | ±50 | mA |
| Power dissipation | PD | 500 (DIP) (Note 2)/180 (SOP) | mW |
| Storage temperature | T _{stg} | –65 to 150 | °C |

Note 1: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 2: 500 mW in the range of Ta = -40 to $65^{\circ}C$. From Ta = 65 to $85^{\circ}C$ a derating factor of -10 mW/°C shall be applied until 300 mW.



Operating Ranges (Note)

| Characteristics | Symbol | Rating | Unit |
|-----------------------|------------------|----------------------|------|
| Supply voltage | V _{CC} | 2 to 6 | V |
| Input voltage | V _{IN} | 0 to V _{CC} | V |
| Output voltage | V _{OUT} | 0 to V _{CC} | V |
| Operating temperature | T _{opr} | -40 to 85 | °C |

Note: The operating ranges must be maintained to ensure the normal operation of the device. Unused inputs must be tied to either VCC or GND.

Electrical Characteristics

DC Characteristics

| Characteristics Symbol | | Test Condition $V_{CC}\left(V\right)$ | | - | Га = 25°(| | Ta = -40 to 85°C | | Unit | |
|------------------------------|-----------------|---|----------------------------|-----|-----------|------|---------------------|------|-------|----|
| | | | | Min | Тур. | Max | Min | Max | Offic | |
| | | | | | 1.0 | 1.25 | 1.50 | 1.0 | 1.50 | |
| Positive threshold voltage | V _P | _ | | 4.5 | 2.3 | 2.70 | 3.15 | 2.3 | 3.15 | V |
| Ğ | | | | 6.0 | 3.0 | 3.50 | 4.20 | 3.0 | 4.20 | |
| | | | | 2.0 | 0.30 | 0.65 | 0.9 | 0.30 | 0.9 | |
| Negative threshold voltage | V_N | | _ | 4.5 | 1.13 | 1.60 | 2.0 | 1.13 | 2.0 | V |
| | | | | 6.0 | 1.50 | 2.30 | 2.6 | 1.50 | 2.6 | |
| | | | | 2.0 | 0.3 | 0.6 | 1.0 | 0.3 | 1.0 | |
| Hysteresis output voltage | V_{H} | _ | | 4.5 | 0.6 | 1.1 | 1.4 | 0.6 | 1.4 | V |
| | | | | | 0.8 | 1.2 | 1.7 | 0.8 | 1.7 | |
| | | V _{IN} = V _{IH} or V _{IL} | | 2.0 | 1.9 | 2.0 | _ | 1.9 | _ | |
| | | | $I_{OH} = -20 \mu A$ | 4.5 | 4.4 | 4.5 | _ | 4.4 | _ | |
| High-level output voltage | V _{OH} | | | 6.0 | 5.9 | 6.0 | _ | 5.9 | _ | V |
| | | | $I_{OH} = -4 \text{ mA}$ | 4.5 | 4.18 | 4.31 | _ | 4.13 | _ | |
| | | | $I_{OH} = -5.2 \text{ mA}$ | 6.0 | 5.68 | 5.80 | _ | 5.63 | _ | |
| | | | | 2.0 | _ | 0.0 | 0.1 | _ | 0.1 | |
| | | | $I_{OL} = 20 \mu A$ | 4.5 | _ | 0.0 | 0.1 | _ | 0.1 | |
| Low-level output voltage Vol | V_{OL} | V _{IN} = V _{IH} or V _{IL} | | 6.0 | _ | 0.0 | 0.1 | _ | 0.1 | V |
| | | | I _{OL} = 4 mA | 4.5 | _ | 0.17 | 0.26 | _ | 0.33 | |
| | | | $I_{OL} = 5.2 \text{ mA}$ | 6.0 | _ | 0.18 | 0.26 | _ | 0.33 | |
| Input leakage current | I _{IN} | V _{IN} = V _{CC} or GND | | 6.0 | _ | _ | ±0.1 | _ | ±1.0 | μΑ |
| Quiescent supply current | I _{CC} | V _{IN} = V _{CC} or | GND | 6.0 | | _ | 1.0 | | 10.0 | μΑ |

AC Characteristics ($C_L = 15 \text{ pF}$, $V_{CC} = 5 \text{ V}$, $Ta = 25^{\circ}\text{C}$, input: $t_r = t_f = 6 \text{ ns}$)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|------------------------|------------------|----------------|-----|------|-----|------|
| Output transition time | tTLH | _ | _ | 4 | 8 | ns |
| | t _{THL} | | | | | |
| Propagation delay time | t _{pHL} | _ | | 11 | 18 | ns |

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AC Characteristics ($C_L = 50 \text{ pF}$, input: $t_r = t_f = 6 \text{ ns}$)

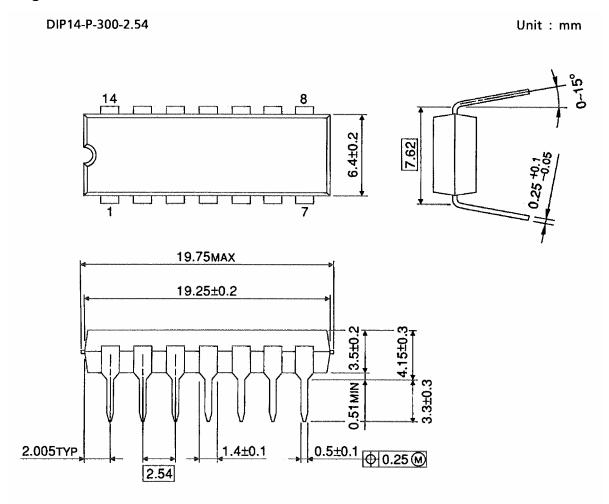
| Characteristics Sy | Symbol Test Condition | Test Condition | | Ta = 25°C | | | Ta = -40 to 85°C | | Unit |
|-------------------------------|------------------------|---------------------|-----|-----------|-----|-----|---------------------|-----|------|
| | | V _{CC} (V) | Min | Тур. | Max | Min | Max | | |
| | 4 — | | 2.0 | _ | 30 | 75 | _ | 95 | |
| Output transition time | t _{TLH} | _ | 4.5 | _ | 8 | 15 | _ | 19 | ns |
| | t _{THL} | | 6.0 | _ | 7 | 13 | _ | 16 | |
| time | t _{pLH} | | 2.0 | _ | 42 | 110 | _ | 140 | |
| | | _ | 4.5 | _ | 14 | 22 | _ | 28 | ns |
| | t _{pHL} | | 6.0 | _ | 12 | 19 | _ | 24 | |
| Input capacitance | C _{IN} | _ | | _ | 5 | 10 | _ | 10 | pF |
| Power dissipation capacitance | C _{PD} (Note) | _ | | _ | 29 | _ | _ | _ | pF |

Note: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

$$I_{CC}$$
 (opr) = $C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/4$ (per gate)

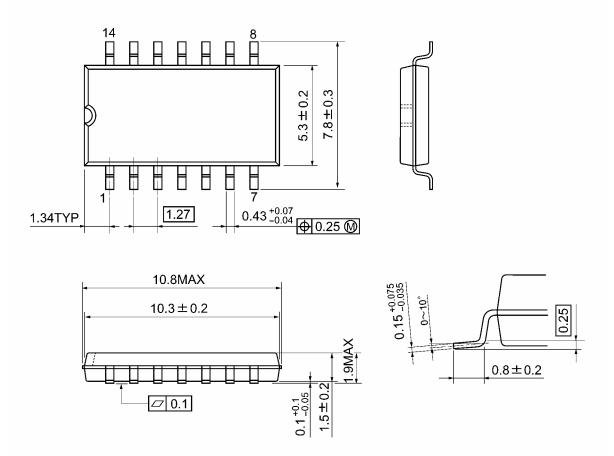
Package Dimensions



Weight: 0.96 g (typ.)

Package Dimensions

SOP14-P-300-1.27A Unit: mm

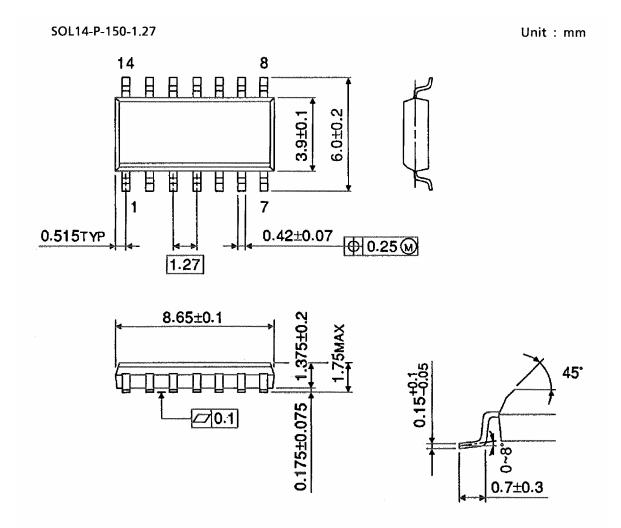


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Weight: 0.18 g (typ.)



Package Dimensions (Note)



Note: This package is not available in Japan.

Weight: 0.12 g (typ.)

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20070701-EN GENERAL

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